



16N50-MT

Power MOSFET

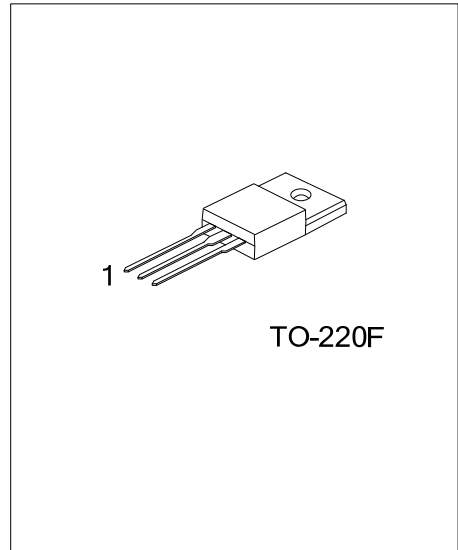
16A, 500V N-CHANNEL POWER MOSFET

DESCRIPTION

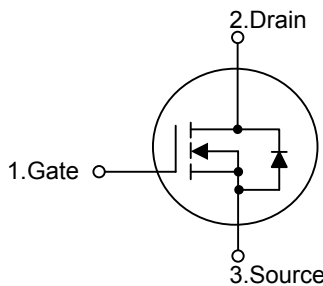
The UTC **16N50-MT** is a N-channel power MOSFET using UTC's advanced technology to provide the customers with minimum on-state resistance, superior switching performance and withstand high energy pulse in the avalanche and commutation mode.

FEATURES

- * $R_{DS(ON)} \leq 0.32\Omega$ @ $V_{GS}=10V, I_D=8.0A$
- * High Switching Speed



SYMBOL



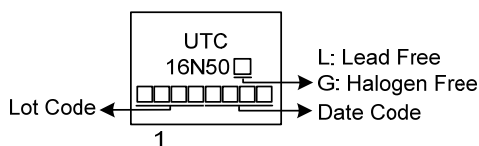
ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen-Free		1	2	3	
16N50L-TF3-T	16N50G-TF3-T	TO-220F	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>16N50G-TF3-T</p> <ul style="list-style-type: none"> (1)Packing Type (2)Package Type (3)Green Package 	<ul style="list-style-type: none"> (1) T: Tube (2) TF3: TO-220F (3) G: Halogen Free and Lead Free, L: Lead Free
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MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_c=25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	500	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current	Continuous	I_D	16	A
	Pulsed (Note 2)	I_{DM}	32	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	757	mJ
Peak Diode Recovery dv/dt		dv/dt	3.9	V/ns
Power Dissipation		P_D	38	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. $L = 10\text{mH}$, $I_{AS} = 12.3\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} \leq 16\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER	SYMBOL	RATING	UNIT
Junction to Ambient	θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
Junction to Case	θ_{JC}	3.29	$^\circ\text{C}/\text{W}$

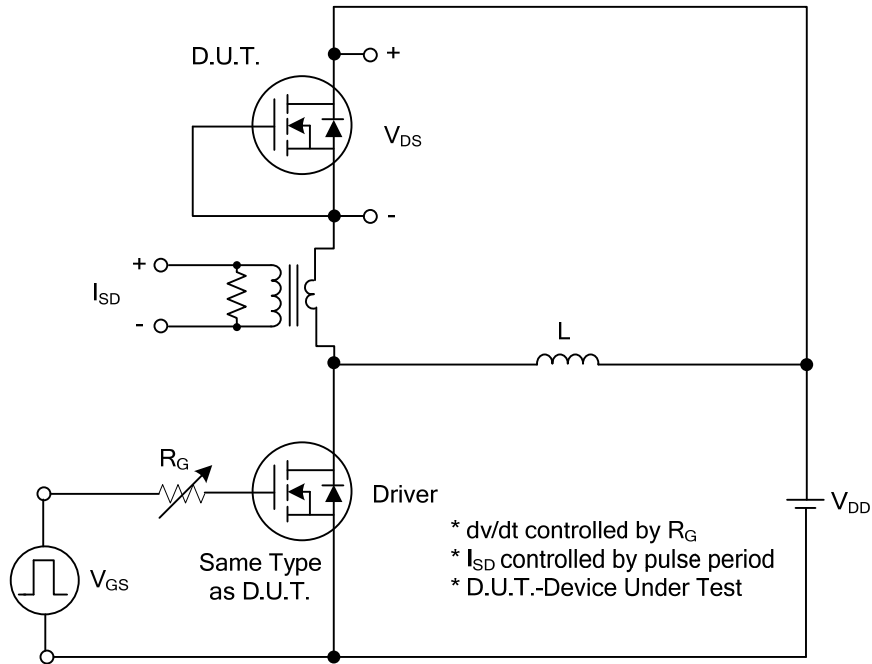
■ ELECTRICAL CHARACTERISTICS ($T_J=25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	500			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=500\text{V}$, $V_{GS}=0\text{V}$			10	μA
Gate- Source Leakage Current	Forward	I_{GSS}			+100	nA
	Reverse				-100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	2.0		4.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10\text{V}$, $I_D=8.0\text{A}$			0.32	Ω
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	$V_{GS}=0\text{V}$, $V_{DS}=25\text{V}$, $f=1.0\text{MHz}$		2270		pF
Output Capacitance	C_{OSS}			255		pF
Reverse Transfer Capacitance	C_{RSS}			13		pF
SWITCHING PARAMETERS						
Total Gate Charge (Note 1)	Q_G	$V_{DS}=100\text{V}$, $V_{GS}=10\text{V}$, $I_D=16\text{A}$ $I_G=1\text{mA}$ (Note1, 2)		48		nC
Gate to Source Charge	Q_{GS}			10		nC
Gate to Drain Charge	Q_{GD}			9		nC
Turn-ON Delay Time (Note 1)	$t_{D(ON)}$	$V_{DS}=100\text{V}$, $V_{GS}=10\text{V}$, $I_D=16\text{A}$, $R_G=25\Omega$ (Note1, 2)		28		ns
Rise Time	t_R			22		ns
Turn-OFF Delay Time	$t_{D(OFF)}$			150		ns
Fall-Time	t_F			36		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Continuous Drain-Source Diode Forward Current	I_S				16	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}				32	A
Drain-Source Diode Forward Voltage (Note 1)	V_{SD}	$I_S=16\text{A}$, $V_{GS}=0\text{V}$			1.4	V
Body Diode Reverse Recovery Time (Note 1)	t_{rr}	$I_S=16\text{A}$, $V_{GS}=0\text{V}$,		380		ns
Reverse Recovery Charge	Q_{rr}	$dI_F/dt=100\text{A}/\mu\text{s}$ (Note 1)		5.4		μC

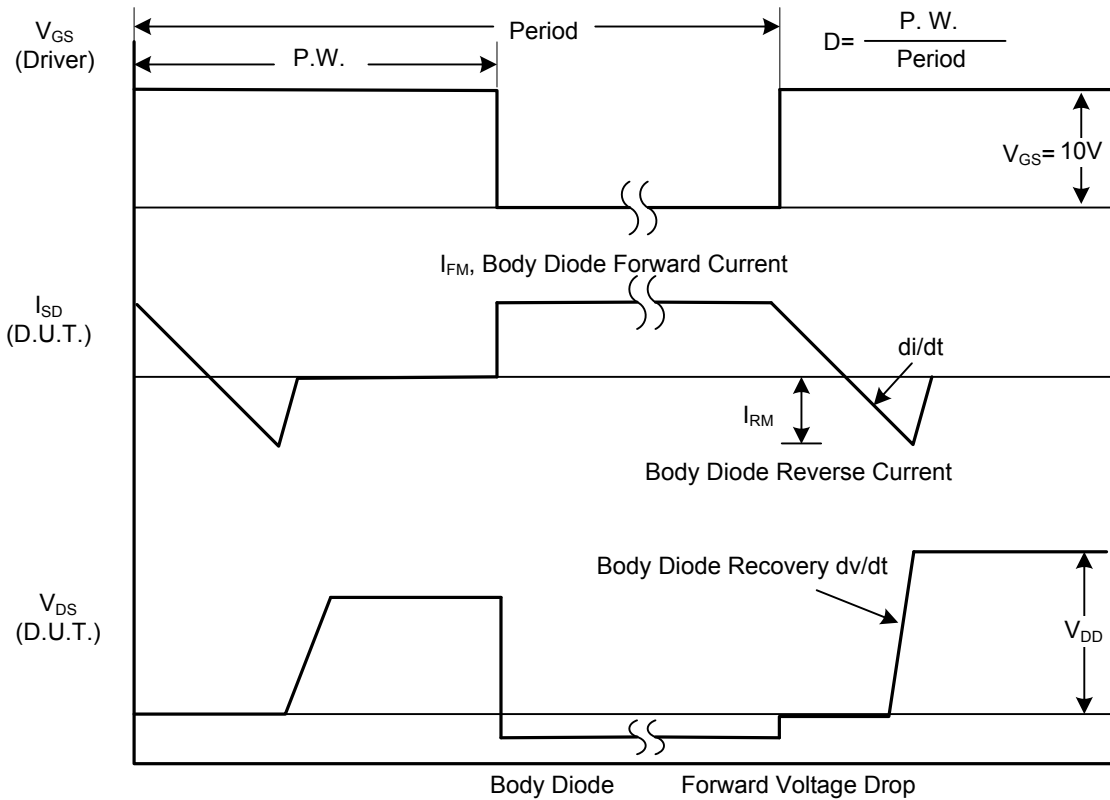
Notes: 1. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

TEST CIRCUITS AND WAVEFORMS

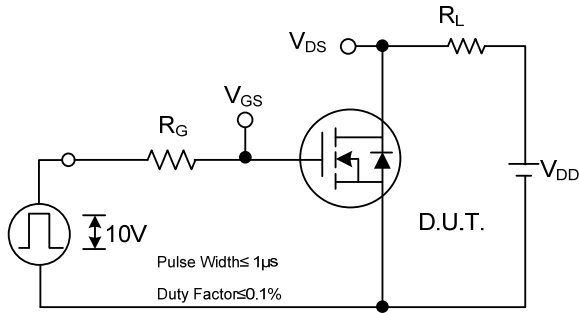


Peak Diode Recovery dv/dt Test Circuit

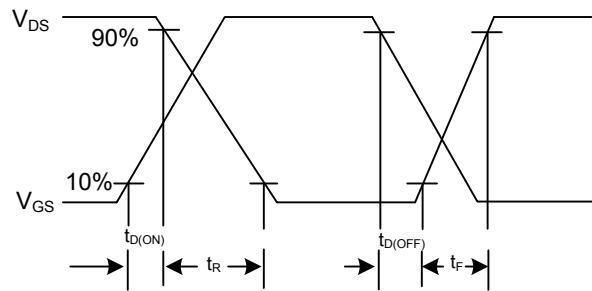


Peak Diode Recovery dv/dt Waveforms

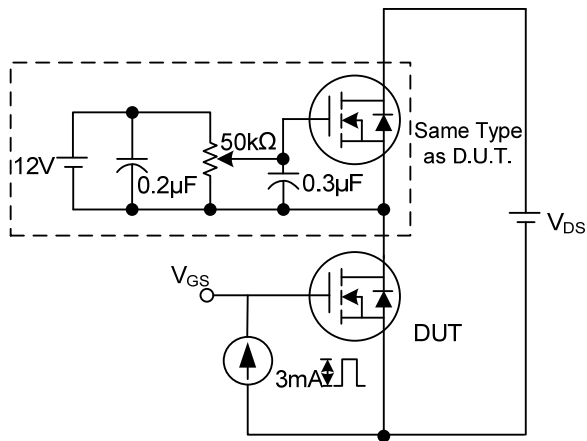
TEST CIRCUITS AND WAVEFORMS



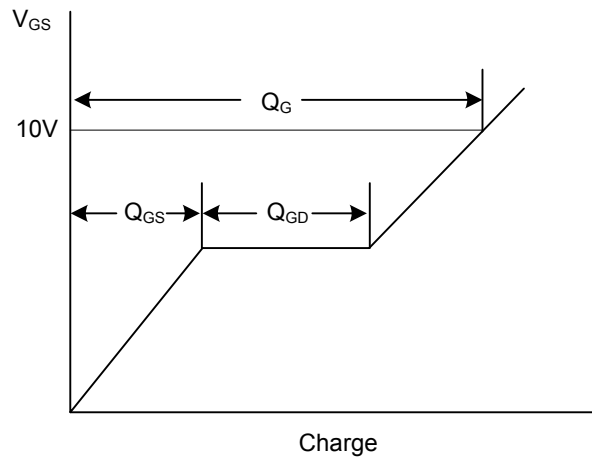
Switching Test Circuit



Switching Waveforms

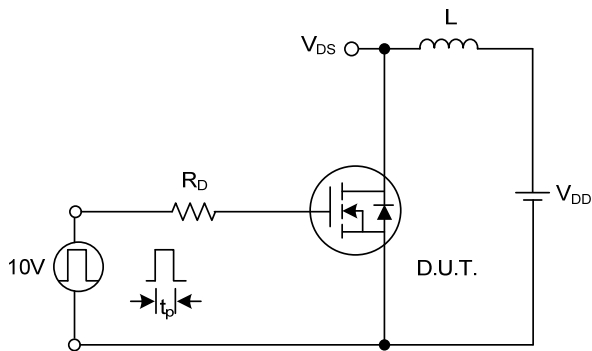


Gate Charge Test Circuit

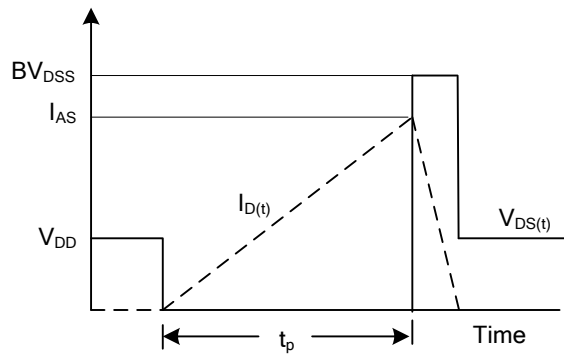


Charge

Gate Charge Waveform

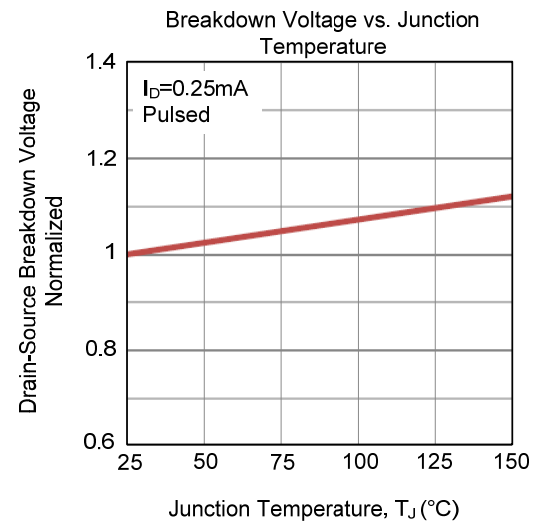
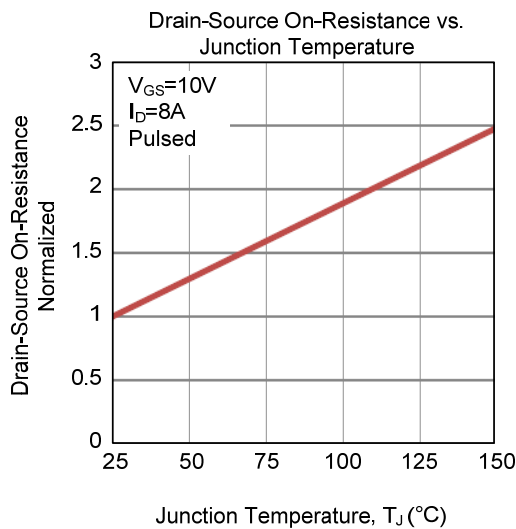
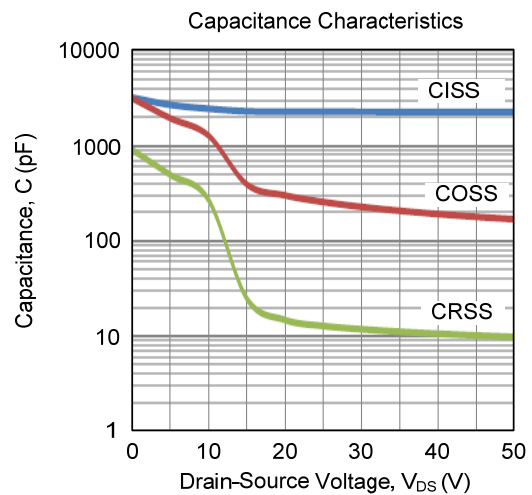
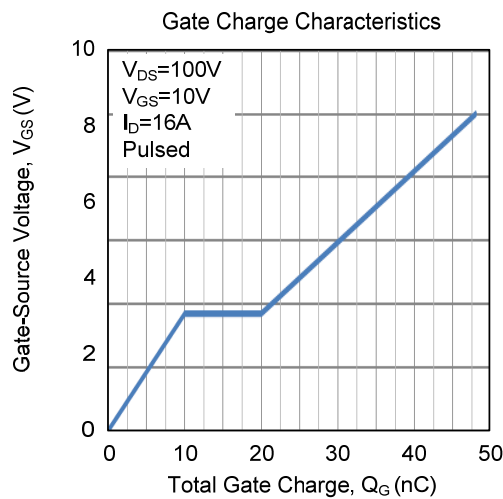
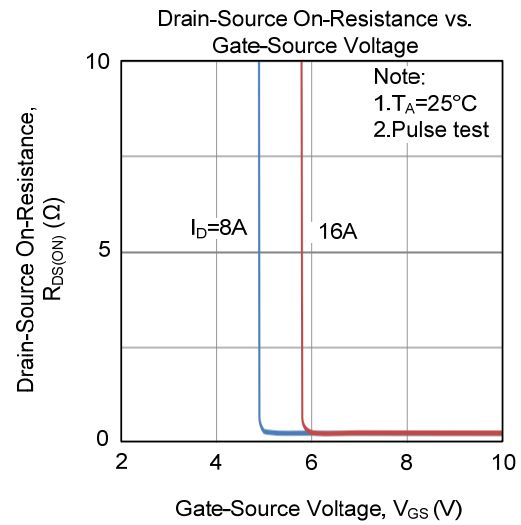
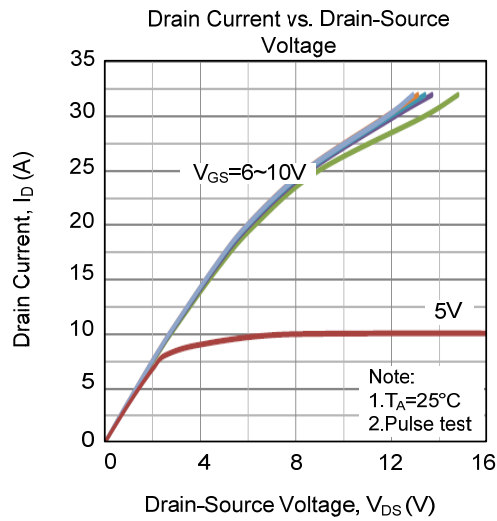


Unclamped Inductive Switching Test Circuit

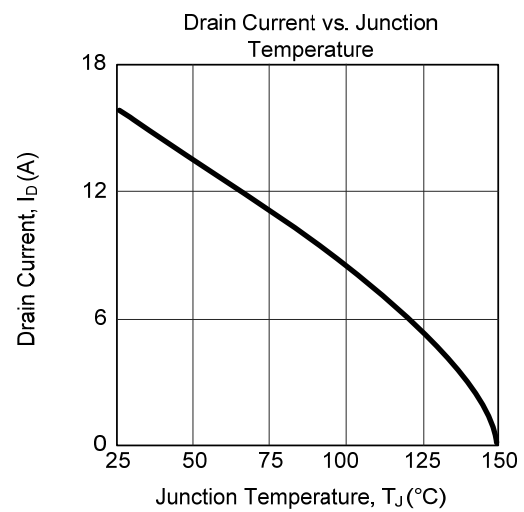
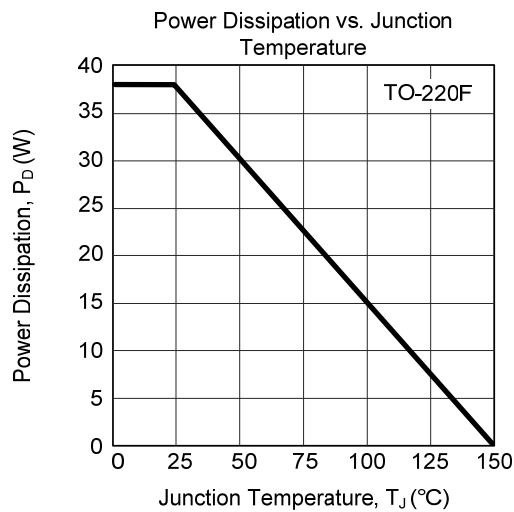
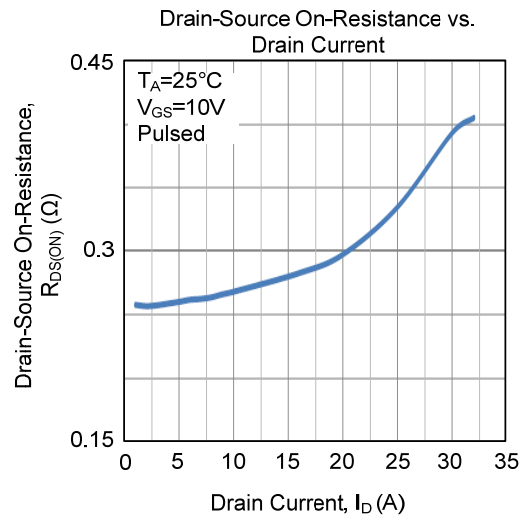
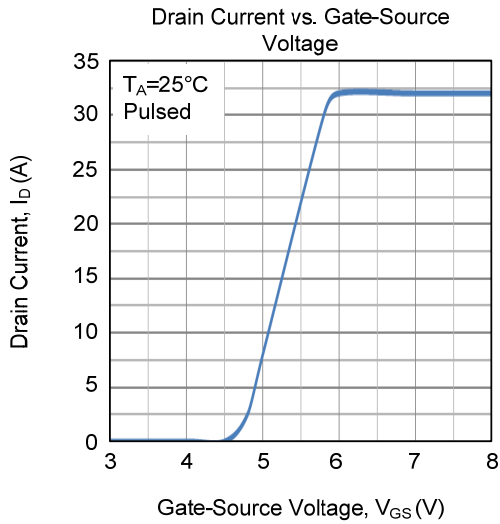
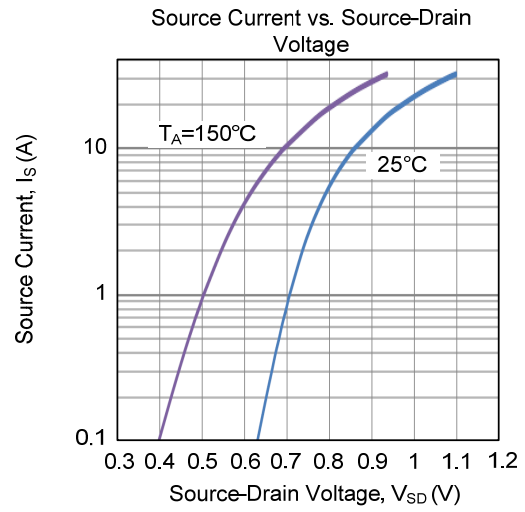
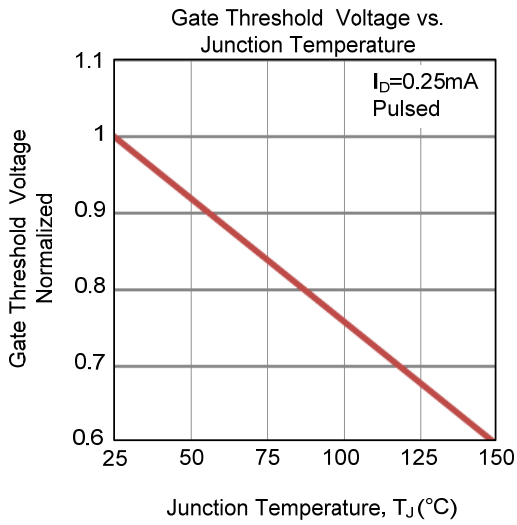


Unclamped Inductive Switching Waveforms

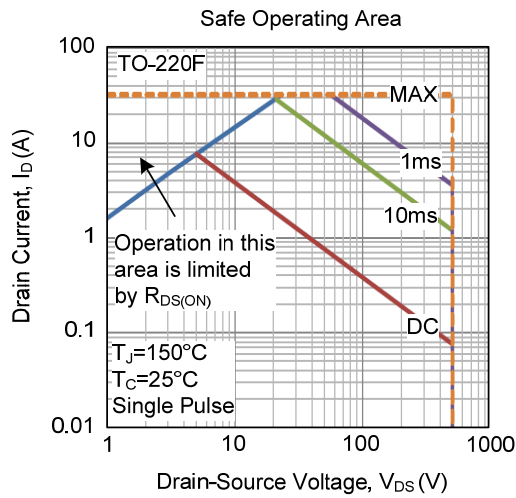
TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS (Cont.)



■ TYPICAL CHARACTERISTICS (Cont.)



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